

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Peter Rabkin et al.

Application No.:

Filed: Herewith

For: TRANSISTOR AND MEMORY
CELL WITH ULTRA-SHORT GATE
FEATURE AND METHOD OF
FABRICATING THE SAME

Examiner: To be Assigned

Art Unit: To be Assigned

PRELIMINARY AMENDMENT

March 13, 2001

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks.

IN THE TITLE:

Please change the Title of the invention to:

--TRANSISTOR WITH ULTRA-SHORT GATE FEATURE AND METHOD OF
FABRICATING THE SAME--.

IN THE SPECIFICATION:

At **page 1, line 4**, please add the following new heading and paragraph:

--CROSS-REFERENCES TO RELATED APPLICATIONS

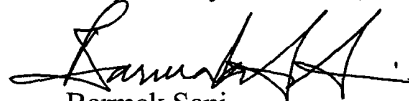
This is a Division of U.S. Application No. 09/797,863 (Atty. Docket No. 00939A-079300US), filed March 1, 2001, and entitled "Transistor and Memory Cell with Ultra-Short Gate Feature and Method of Fabricating the Same", the disclosure of which is incorporated herein by reference.--

IN THE CLAIMS:

Please cancel claims 19-76 and 90-99.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 650-326-2400.

Respectfully submitted,



Barmak Sani
Reg. No. 45,068

TOWNSEND and TOWNSEND and CREW LLP
Two Embarcadero Center, 8th Floor
San Francisco, California 94111-3834
Tel: (415) 576-0200
Fax: (415) 576-0300
BXS:gjs
PA 3132623 v1

TELEPHONE